CLAIMS

1. A crushed polycrystalline silicon lump,

wherein a surface metal concentration is 15.0 pptw or less, and in the surface metal concentration, a surface tungsten concentration is 0.9 pptw or less, and a surface cobalt concentration is 0.3 pptw or less.

2. The crushed polycrystalline silicon lump according to claim 1,

wherein the surface metal concentration is 7.0 to 13.0 pptw, and in the surface metal concentration, the surface tungsten concentration is 0.40 to 0.85 pptw, and the surface cobalt concentration is 0.04 to 0.08 pptw.

3. The crushed polycrystalline silicon lump according to claims 1 or 2,

wherein the surface metal concentration is a total concentration of Na, Mg, Al, K, Ca, Cr, Fe, Ni, Co, Cu, Zn, W, Ti, and Mo.

4. A crushed polycrystalline silicon lump package,

wherein the crushed polycrystalline silicon lump according to any one of claims 1 to 3 is accommodated in a resin bag.

5. A method for manufacturing the crushed polycrystalline silicon lump according to claim 1, comprising:

a) a step of crushing a polycrystalline silicon rod;

b) a first washing step of contacting the crushed lump of the polycrystalline silicon rod with a fluonitric acid aqueous solution;

c) a second washing step of contacting the crushed polycrystalline silicon lump

that has undergone to the first washing step with an alkali aqueous solution containing hydrogen peroxide; and

d) a third washing step of contacting the crushed polycrystalline silicon lump that has undergone the second washing step with the fluonitric acid aqueous solution.

6. The method for manufacturing crushed polycrystalline silicon lump according to claim 5,

wherein in the c) second washing step, an alkaline substance dissolved in the alkali aqueous solution containing hydrogen peroxide is tetramethyl ammonium hydroxide.

7. The method for manufacturing crushed polycrystalline silicon lump according to claim 5 or 6,

wherein in the a) step of crushing the polycrystalline silicon rod, a breaking tool in which a material of a striking part is composed of a tungsten carbide/cobalt alloy is used in the crushing.

8. The method for manufacturing a crushed polycrystalline silicon lump according to any one of claims 5 to 7,

wherein in the b) first washing step, an etching amount of a surface of each crushed polycrystalline silicon lump is 1.5 to 10.0 μm.